

MOS FIELD EFFECT TRANSISTOR μ PA2502

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA2502, which has a heat spreader, is N-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of notebook computers.

FEATURES

- μ PA2502 has a thin surface mount package with a heat spreader. The land size is same as 8-pin TSSOP.
- Low on-state resistance

 $R_{DS(on)1} = 12.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 10.0 \text{ V, I}_D = 7.0 \text{ A)}$

 $R_{DS(on)2}$ = 18.0 m Ω MAX. (Vgs = 4.5 V, ID = 7.0 A)

• Low Ciss: 760 pF TYP. (VDS = 10.0 V, VGS = 0 V)

ORDERING INFORMATION

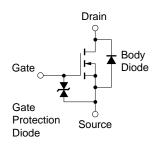
PART NUMBER	PACKAGE
μ PA2502TM	8PIN HWSON

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

•	•		
Drain to Source Voltage (V _{GS} = 0 V)	VDSS	30.0	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20.0	V
Drain Current (DC) Note1	ID(DC)	±13.0	Α
Drain Current (pulse) Note2	I _{D(pulse)}	±52.0	Α
Total Power Dissipation Note1	Рт	2.7	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note3	las	13.0	Α
Single Avalanche Energy Note3	Eas	16.9	mJ

- **Notes 1.** Mounted on FR-4 board of 25 cm² x 1.6 mm, PW ≤ 10 sec
 - **2.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - 3. Starting Tch = 25°C, VDD = 15.0 V, Rg = 25 Ω , Vgs = 20.0 \rightarrow 0 V

EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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ELECTRICAL CHARACTERISTICS (TA = 25°C)

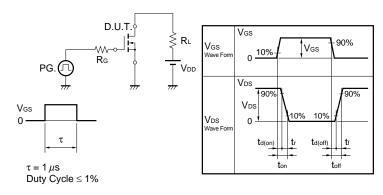
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30.0 V, V _{GS} = 0 V			1.0	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20.0 V, V _{DS} = 0 V			±10.0	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10.0 V, I _D = 1.0 mA	1.50		2.50	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10.0 V, I _D = 7.0 A	5			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10.0 V, I _D = 7.0 A		9.3	12.0	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 7.0 A		13.1	18.0	mΩ
Input Capacitance	Ciss	V _{DS} = 10.0 V		760		pF
Output Capacitance	Coss	V _{GS} = 0 V		300		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		100		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15.0 V, I _D = 7.0 A		14		ns
Rise Time	tr	V _{GS} = 10.0 V		3		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		32		ns
Fall Time	t _f			4		ns
Total Gate Charge	Q _G	V _{DD} = 15.0 V		8.5		nC
Gate to Source Charge	Qgs	V _{GS} = 5.0 V		2.8		nC
Gate to Drain Charge	Q _{GD}	I _D = 13.0 A		3.5		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 13.0 A, V _{GS} = 0 V		0.84		V
Reverse Recovery Time	trr	I _F = 13.0 A, V _{GS} = 0 V		27		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		24		nC

Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ V_{DD} V_{DD}

TEST CIRCUIT 2 SWITCHING TIME



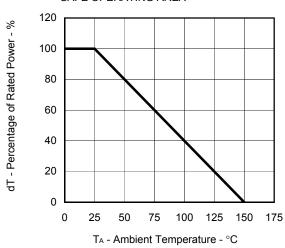
TEST CIRCUIT 3 GATE CHARGE

$$\begin{array}{c|c} D.U.T. \\ \hline \\ I_G = 2 \text{ mA} \\ \hline \\ \hline \\ V_{DD} \\ \hline \end{array}$$

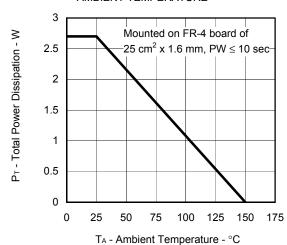
Starting Tch

TYPICAL CHARACTERISTICS (TA = 25°C)

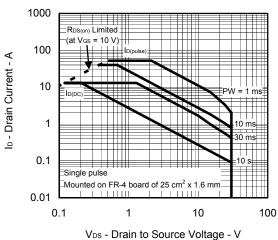
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



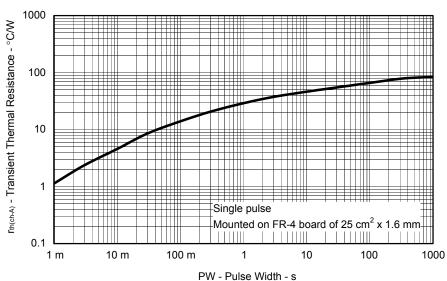
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA

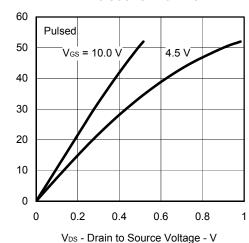


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

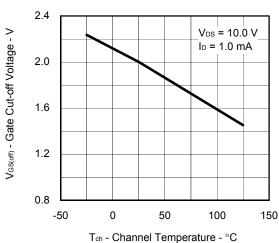


lo - Drain Current - A

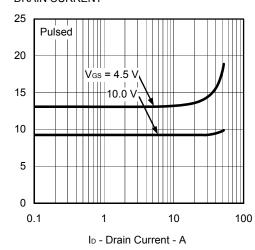
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



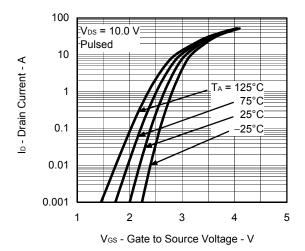
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



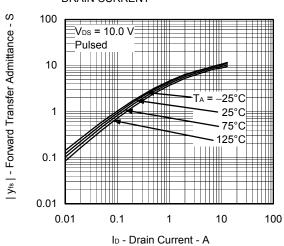
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



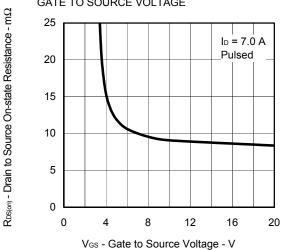
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



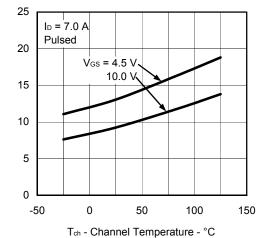
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



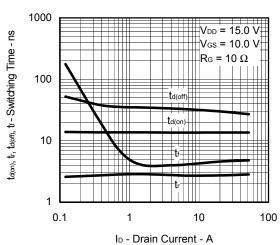
R_{DS(on)} - Drain to Source On-state Resistance - mΩ

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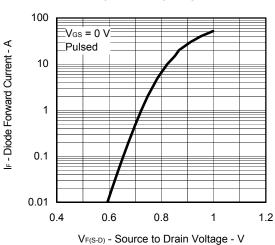




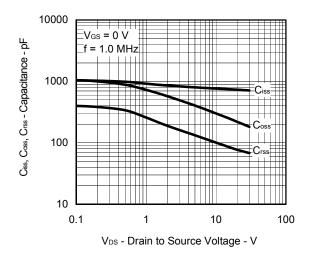
SWITCHING CHARACTERISTICS



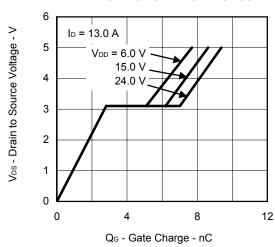
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



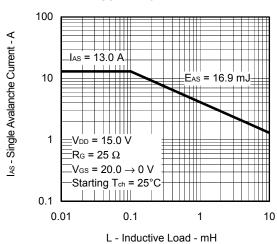
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DYNAMIC INPUT CHARACTERISTICS

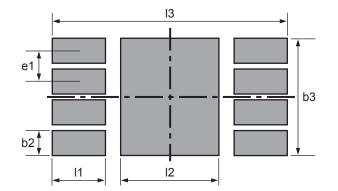


SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



EXAMPLE OF THE LAND PATTERN

Please optimize the land pattern in consideration of density, appearance of solder fillets, common difference, etc in an actual design.



e1: 0.65

b2: 0.35

b3: 2.7

I1: 1.3

12: 3.7

I3: 7.1

(Unit: mm)

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